

# NPN SILICON RF POWER TRANSISTOR

**DESCRIPTION:**

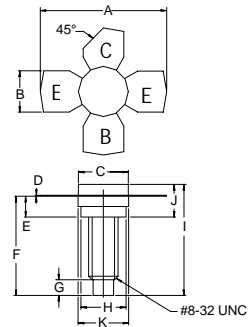
The **ASI MLN 1005-28S** is a Common Emitter Device Designed for General Purpose Class A and AB Amplifier Applications up to 1200 MHz.

**FEATURES INCLUDE:**

- Gold Metalization
- Emitter Ballasting
- High Gain

**MAXIMUM RATINGS**

<b>I<sub>C</sub></b>	1.5 A
<b>V<sub>CES</sub></b>	65 V
<b>P<sub>DISS</sub></b>	32 W @ T <sub>C</sub> = 25 °C
<b>T<sub>J</sub></b>	-65 to +200 °C
<b>T<sub>STG</sub></b>	-65 to +150 °C
<b>θ<sub>JC</sub></b>	5.5 °C/W

**PACKAGE STYLE .280" 4L STUD**


DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	1.010 / 25.65	1.055 / 26.80
B	.220 / 5.59	.230 / 5.84
C	.270 / 6.86	.285 / 7.24
D	.003 / 0.08	.007 / 0.18
E	.117 / 2.97	.137 / 3.48
F	.572 / 14.53	
G	.130 / 3.30	
H	.245 / 6.22	.255 / 6.48
I	.640 / 16.26	
J	.175 / 4.45	.217 / 5.51
K	.275 / 6.99	.285 / 7.24

**CHARACTERISTICS** T<sub>C</sub> = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
<b>BV<sub>CES</sub></b>	I <sub>C</sub> = 10 mA	65			<b>V</b>
<b>BV<sub>CEO</sub></b>	I <sub>C</sub> = 5 mA	25			<b>V</b>
<b>BV<sub>EBO</sub></b>	I <sub>E</sub> = 5.0 mA	4.0			<b>V</b>
<b>h<sub>FE</sub></b>	V <sub>CE</sub> = 5.0 V      I <sub>C</sub> = 500 mA	20		200	<b>---</b>
<b>C<sub>OB</sub></b>	V <sub>CB</sub> = 28 V      f = 1.0 MHz		15	20	<b>pF</b>
<b>P<sub>G</sub></b> <b>P<sub>1dB</sub></b>	V <sub>CE</sub> = 25 V      I <sub>CQ</sub> = 850 mA      f = 1.0 GHz	8.0 5.0	10		<b>dB</b> <b>W</b>